In the Claims:

Please amend the claims as follows:

- 1. (Currently Amended) A memory comprising:
- at least one array of memory elements;
- a partition of the at least one array into a plurality of sub-arrays of the memory elements:

an array configuration circuit for selectively putting the at least one array in one of two operating configurations, the two operating configurations including:

a first operating configuration, in which the memory elements of the at least one array are coupled one to another to form a monodimensional sequentially-accessible memory, and

a second operating configuration, in which the memory elements in each sub-array are coupled to one another so as to form an independent monodimensional sequentially-accessible memory block, a data content of any memory element of the sub-array being rotatable by shifts through the memory elements of the sub-array;

a sub-array selector, responsive to a first memory address, for selecting one among the at least twoplurality of sub-arrays according to the first memory address, the sub-array selector enabling access to the selected sub-array; and

a memory element access circuit, responsive to a second memory address, for enabling access to a prescribed memory element in the selected sub-array after a prescribed number of shifts, depending on the second memory address, of the data content of the memory elements in the selected sub-array.

2. (Original) The memory according to claim 1, in which said array configuration circuit includes, for each sub-array of memory elements, an input selector associated with a first memory element of the sub-array, for selectively feeding the first memory element with either an output of a last memory element in an adjacent previous sub-array, in the first operating configuration, or an output of a last memory element of the sub-array, in the second operating configuration.

- 3. (Original) The memory according to claim 1, in which the first operating configuration is a data storage configuration, in which the memory is put when data are to be stored therein, and the second operating configuration is a data retrieval configuration, in which the memory is put when data are to be retrieved therefrom.
- 4. (Currently Amended) The memory according to claim 3, in which in the second operating configuration each sub-array provides a respective output data, the sub-array selector selecting one sub-array output data out of the at least two output data provided by the at least two plurality of sub-arrays, according to the first address.
- 5. (Original) The memory according to claim 4, in which said memory element access circuit enables a transfer of the output data of the selected sub-array to a memory output after a prescribed number of shifts of the data content of the memory elements in the selected sub-array.
- 6. (Original) The memory according to claim 5, in which said memory element access circuit includes a counter for counting the number of data content shifts, and a coincidence detector detecting coincidence between a counter value and a value representative of the second address, the coincidence detector enabling the transfer of the output data of the selected sub-array to the memory output when the counter value equals the value representative of the second address.
- 7. (Original) The memory according to claim 1, in which each memory element includes at least one flip-flop.
 - 8. (Original) A memory, comprising:
 - a plurality of memory locations each having a contents; and
 - a control circuit coupled to the memory locations and operable to,
 - allow random access to the memory locations during a first mode of operation, and

allow sequential access to the contents of the memory locations via a predetermined one of the memory locations during a second mode of operation.

- 9. (Original) The memory of claim 8 wherein: the first mode of operation comprises a read mode; and the second mode of operation comprises a write mode.
- 10. (Original) The memory of claim 8 wherein: the first mode of operation comprises a write mode; and the second mode of operation comprises a read mode.
- 11. (Cancelled)
- 12. (Currently Amended) A memory, comprising:

an array of memory locations; and

a control circuit coupled to the array and operable to cause the array to operate as

a random-access memory during a first mode of operation, and

a first-in-first-out memory during a second mode of operation,

The memory of claim 11-wherein:

the memory locations comprise a-rings of serially coupled memory locations each having a respective contents, with the contents of each ring being independent of the contents of the other rings; and

during the first mode of operation, the control circuit is operable to <u>control each of</u> the rings to,

receive a clock signal,

shift the contents of each respective memory location in the ring to a respective next memory location in the ring once per cycle of the clock signal, and allow access to a predetermined one of the memory locations during a predetermined cycle of the clock signal.

13. (Currently Amended) The memory of claim 11-12 wherein:

the memory locations comprise a ring of a number n of serially coupled memory locations each having a respective contents; and

during the first mode of operation, the control circuit is operable to, receive a clock signal,

shift the contents of each respective memory location in the ring to a respective next memory location in the ring once per cycle of the clock signal for *n* clock cycles, and

allow access to a predetermined one of the memory locations during a predetermined cycle of the clock signal.

14. (Original) An electronic system, comprising: a memory, comprising,

a plurality of memory locations each having a contents, and a control circuit coupled to the memory locations and operable to,

allow random access to the memory locations during a first mode of operation, and

allow sequential access to the contents of the memory locations via a predetermined one of the memory locations during a second mode of operation.

15. (Original) A method, comprising:

randomly accessing memory locations of a memory during a first mode of operation, and

sequentially accessing the contents of the memory locations via a predetermined one of the memory locations during a second mode of operation.

16. (Original) The method of claim 15 wherein randomly accessing the memory locations comprises:

accessing a first memory location having a first address; and accessing a second memory location having a second address.

17. (Original) The method of claim 15 wherein sequentially accessing the memory locations comprises:

reading first data from a first memory location;

shifting second data from a second memory location into the first memory location; and

reading the second data from the first memory location.

18. (Original) The method of claim 15 wherein sequentially accessing the memory locations comprises:

writing first data to a first memory location;

shifting the first data from the first memory location to a second memory location; and

writing second data to the first memory location.

19. (Original) The method of claim 15 wherein randomly accessing the memory locations comprises:

shifting the contents of each respective memory location to a respective next memory location a number of times; and

accessing a predetermined one of the memory locations after a predetermined one of the shifts.

20. (Original) The method of claim 15 wherein randomly accessing the memory locations comprises:

shifting the contents of each of n respective memory locations to a respective next one of the n memory locations n times; and

accessing a predetermined one of the n memory locations after a predetermined one of the n shifts.